AUG 1 8 2003

Docket No. 0756-2351

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of Shunpei YAMAZAKI et al.

Serial No. 09/932.935

Filed: August 21, 2001

For: LASER APPARATUS, LASER

ANNEALING METHOD, AND

MANUFACTURING METHOD OF A

SEMICONDUCTOR DEVICE

Art Unit: 2812

Examiner: V. Simkovic

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on 9.15.2003.

Adele M. Stamper

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 3.97 1.99 Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The present application is the parent of U.S. Patent Application Publication No. 2002/0048864.

As a supplement to the Information Disclosure Statement filed January 25, 2002. the Applicants submit the cover page of Helen et al., "Reproducible High Field Effect Polysilicon Thin Film Transistors Involved Pulsed Nd:YVO₄ Laser Crystallization," pp. 297-300, 1999, IEDM 0-7803-5410-9/99 IEEE, which shows that the publication of the Helen reference was December 5-8, 1999.

This Information Disclosure Statement is being submitted with an RCE. Therefore, no fee is required.

Application No. 09/932,935 Docket No. 0756-2351

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 50-2280. A duplicate copy of this sheet is attached.

Respectfully submitted,

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INFO	RMATIC	N DISC	LOSURE	Application Number	09/932,935	
				Filing Date	August 21, 2001	
STATEMENT BY APPLICANT				First Named Inventor	Shunpei YAMAZAKI et al.	
	(use as many .	sheets as necess	ary)	Group Art Unit	2812	
				Examiner Name	V. Simkovic	
Sheet	1	of	1	Attorney Docket Number	0756-2351	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number Kind Code (if known)				
		2002/0048864	Yamazaki et al.	04/25/2002		
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		Cover page of Helen et al., "Reproducible High Field Effect Mobility Polysilicon Thin Film Transistors Involved Pulsed Nd:YVO ₄ Laser Crystallization," pp. 297-300, IEDM 7803-5410-9/99 IEEE, December 5-8, 1999.						
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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